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	Application No.	Applicant(s)	/
Notice of Allowability	10/711,182	ZHU ET AL.	
	Examiner	Art Unit	
	Michael Durbin	2815	
The MAILING DATE of this communication ap All claims being allowable, PROSECUTION ON THE MERITS I nerewith (or previously mailed), a Notice of Allowance (PTOL-8 NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT of the Office or upon petition by the applicant. See 37 CFR 1.3	S (OR REMAINS) CLOSED in 5) or other appropriate commer RIGHTS. This application is s	n this application. If not included unication will be mailed in due cou	rse. THIS
1. This communication is responsive to <u>08/16/2007</u> .		•	
2. \boxtimes The allowed claim(s) is/are $3 - 18$.			
3. Acknowledgment is made of a claim for foreign priority a) All b) Some* c) None of the: 1. Certified copies of the priority documents hat 2. Certified copies of the priority documents hat 3. Copies of the certified copies of the priority of International Bureau (PCT Rule 17.2(a)). * Certified copies not received: Applicant has THREE MONTHS FROM THE "MAILING DATE noted below. Failure to timely comply will result in ABANDON THIS THREE-MONTH PERIOD IS NOT EXTENDABLE. 4. A SUBSTITUTE OATH OR DECLARATION must be sub INFORMAL PATENT APPLICATION (PTO-152) which go so considered by the Notice of Draftsperior (a) including changes required by the Notice of Draftsperior (b) hereto or 2) to Paper No./Mail Date [b) including changes required by the attached Examine Paper No./Mail Date Identifying indicia such as the application number (see 37 CFR each sheet. Replacement sheet(s) should be labeled as such in	ive been received. Ive been received in Application documents have been received. E" of this communication to file IMENT of this application. In itted. Note the attached EX ives reason(s) why the oath of its submitted. I serson's Patent Drawing Reviewer's Amendment / Comment of the comm	on No d in this national stage application a reply complying with the require AMINER'S AMENDMENT or NOTI r declaration is deficient. w (PTO-948) attached r in the Office action of the drawings in the front (not the back	ements
i. ☐ DEPOSIT OF and/or INFORMATION about the department attached Examiner's comment regarding REQUIREMEN			the
Attachment(s) I. ☑ Notice of References Cited (PTO-892) 2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948) 3. ☑ Information Disclosure Statements (PTO/SB/08), Paper No./Mail Date 08/31/2007 4. ☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material	6. Interview S Paper No. 7. Examiner's	formal Patent Application ummary (PTO-413), /Mail Date Amendment/Comment Statement of Reasons for Allowar	nce
4. Examiner's Comment Regarding Requirement for Deposit			/ar

10/711,182 Art Unit: 2815

EXAMINER'S AMENDMENT

1. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

Authorization for this examiner's amendment was given in a telephone interview with H. Daniel Schnurmann (Registration No. 35,791) on 1 November 2007.

The application has been amended as follows:

Claim 1: (Cancelled).

Claim 2: (Cancelled).

Claim 18: (Currently Amended) An integrated circuit including the gated semiconductor device as claimed in claim 4_3.

Claim 19: (Cancelled).

Claim 20: (Cancelled).

Claim 21: (Cancelled).

Claim 22: (Cancelled).

Allowable Subject Matter

2. The following is an examiner's statement of reasons for allowance: Regarding claim 3, the prior art of record, either singularly or in combination, does not disclose or

suggest the combination of limitations including: a first gate consisting essentially of polycrystalline silicon germanium overlying the first side, the first gate having a first gate length in the lateral direction; and a second gate consisting essentially of polysilicon overlying the second side, the second gate having a second gate length in the lateral direction which is different from the first gate length, the second gate being electrically isolated from the first gate.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Conclusion

- 3. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.
 - US 2006/0043616 A1: A fin-type semiconductor device having a multi-part gate including polysilicon and polycrystalline silicon germanium, with no isolation of different gate electrodes.
 - US 2005/0110085 A1: A finFET having two independently addressable gate electrodes.
 - US 6,433,609 B1: MOSFETS, including a finFET, having a dual or double gate layout.

Application/Control Number:

10/711,182 Art Unit: 2815

US 2005/0224890 A1: A finFET device having a gate that is smaller that the main gate

US 2005/0110078 A1: A MOSFET having a back gate with a different gate length than the top gate length.

US 6,787,402 B1: A double gate finFET.

US 2004/0161898 A1: A dual-double-gate finFET.

US 2005/0275040 A1: A finFET SRAM with a backgate.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Michael Durbin whose telephone number is (571) 272-9766. The examiner can normally be reached on M-T 7:30-5; 1st Fri. of biweek off, 2nd 7:30-4.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Ken Parker can be reached on (571) 272-2298. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

10/711,182

Contract.

Art Unit: 2815

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

Michael Durbin Examiner Art Unit 2815

MHD

ory Example